

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Z. Hu et al.

Attorney Docket No.: SEMT116058

Application No.: 10/667,802

Group Art Unit: 1764

Filed:

September 22, 2003

Title:

PLATINUM ALLOY USING ELECTROCHEMICAL DEPOSITION

INFORMATION DISCLOSURE STATEMENT

Seattle, Washington 98101

TO THE COMMISSIONER FOR PATENTS:

Applicants are aware of the information listed in the attached form that may be material to the prosecution of the above-identified patent application.

- 1. \mathbf{X} Copies of the listed WIPO publication and other information are enclosed for the Examiner's use.
- 2. Pursuant to 37 C.F.R. § 1.97(b), this Information Disclosure Statement is being X filed before the mailing date of a first Office Action on the merits.

Respectfully submitted,

CHRISTENSEN O'CONNOR

Jeffrey M. Sakoi

Registration No. 32,059

Direct Dial No. 206.695.1713

I hereby certify that this correspondence is being deposited with the U.S. Postal Service in a sealed envelope as first class mail with postage thereon fully prepaid and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the below date.

INFORMATION CITED BY APPLICANTS THAT MAY BE MATERIAL TO THE PROSECUTION OF THE SUBJECT APPLICATION

Applicant:

Z. Hu et al.

Attorney Docket No. SEMT116058

Application No.: 10/667,802

Group Art Unit: 1764

Filed:

September 22, 2003

Title:

PLATINUM ALLOY USING ELECTROCHEMICAL DEPOSITION

U.S. PATENT DOCUMENTS

*Examiner Cite		Kind	Date	
Initials No.	Document No.	Code	(mm/dd/yyyy)	Name
U1	3,963,523		06/15/1976	Tanaka et al.
U2	4,192,729		03/11/1980	Cancelleri et al.
U3	4,243,532		01/06/1981	Tsuda et al.
U4	4,285,784		08/25/1981	Flinn et al.
U5	4,358,352		11/09/1982	Rhoda
U6	4,427,502		01/24/1984	Abys
U7	4,705,606		11/10/1987	Young et al.
U8	4,750,977		06/14/1988	Marrese
U9	5,232,328		08/03/1993	Owczarz et al.
U10	5,310,475		05/10/1994	Kitada et al.
U11	5,320,978		06/14/1994	Hsu
U12	5,344,491		09/06/1994	Katou
U13	5,421,991		06/06/1995	Yarita
U14	5,484,518		01/16/1996	Goldberg
U15	5,494,560		02/27/1996	Arimoto et al.
U16	5,529,680		06/25/1996	Kitada et al.
U17	5,549,808		08/27/1996	Farooq et al.
U18	5,556,814		09/17/1996	Inoue
U19	5,620,581		04/15/1997	Ang
U20	5,620,583		04/15/1997	Kuhn et al.

Initial No. Document No. Code (mm/dd/yyyy) Country F1 WO 98/02909 A1 01/22/1998 WO OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No.	E)							
U21 5,731,678 03/24/1998 Zila et al.	452		• ==					
U22	<u>Initials</u>	No.	Document No.	. Cod	e (mm/dd/yyyy)	Name		
U23		_ U21	5,731,678		03/24/1998	Zila et al.		
U24		_ U22	5,789,320		08/04/1998	Andricacos et al.		
U25		_ U23	5,972,192		10/26/1999	Dubin et al.		
U26 6,077,412 06/20/2000 Ting et al U27 6,080,291 06/27/2000 Woodruff et al. U28 6,132,587 10/17/2000 Jorne et al. U29 6,140,241 10/31/2000 Shue et al. U30 6,174,425 B1 01/16/2001 Simpson et al. English Abstract Trans FOREIGN PATENT DOCUMENTS *Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided Prov		_ U24	5,985,126		11/16/1999	Bleck et al.		
U27 6,080,291 06/27/2000 Woodruff et al. U28 6,132,587 10/17/2000 Jorne et al. U29 6,140,241 10/31/2000 Shue et al. U30 6,174,425 B1 01/16/2001 Simpson et al. FOREIGN PATENT DOCUMENTS *Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided Prov. F1 WO 98/02909 A1 01/22/1998 WO OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Yo 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO ₃ Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Developmen 43(3):367-382, May 1999.	•	_ U25	6,074,544		06/13/2000	Reid et al.		
U28 6,132,587 10/17/2000 Jorne et al. U29 6,140,241 10/31/2000 Shue et al. U30 6,174,425 B1 01/16/2001 Simpson et al. FOREIGN PATENT DOCUMENTS *Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided No. OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Young 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO3 Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Development 43(3):367-382, May 1999.		_ U26	6,077,412		06/20/2000	Ting et al		
U29 6,140,241 10/31/2000 Shue et al. U30 6,174,425 B1 01/16/2001 Simpson et al. FOREIGN PATENT DOCUMENTS *Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided Provided Provided Provided Provided Provided No. OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Young 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO3 Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Development 43(3):367-382, May 1999.		_ U27	6,080,291		06/27/2000	Woodruff et al.		
*Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided Prov. *Examiner Cite Initial No. Document No. Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No. OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Young 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO3 Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Development 43(3):367-382, May 1999.		_ U28	6,132,587		10/17/2000	Jorne et al.		
*Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided Provided Provided Provided Provided Provided No. OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Young 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO3 Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Development 43(3):367-382, May 1999.		_ U29	6,140,241		10/31/2000	Shue et al.		
*Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided Provided No. Code (mm/dd/yyyy) Country Provided Provid		_ U30	6,174,425	B1	01/16/2001	Simpson et al.		
*Examiner Cite Initial No. Document No. Code (mm/dd/yyyy) Country Provided Provided No. Code (mm/dd/yyyy) Country Provided Provid			FORI	EIGN PA	ATENT DOCUMEN	NTS		
*Examiner Cite							English	
F1 WO 98/02909 A1 01/22/1998 WO OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.) *Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Yo 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO ₃ Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Developmen 43(3):367-382, May 1999.			Document No			Country	Abstract Translation	
*Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Yo 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO ₃ Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Developmen 43(3):367-382, May 1999.	711111111						Provided Provided	
*Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Yo 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO ₃ Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Developmen 43(3):367-382, May 1999.		1 1	WO 30/02303	AI	01/22/1770	****		
*Examiner Cite Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New You 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO ₃ Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Development 43(3):367-382, May 1999.						Doggo Etal)		
Initial No. O1 Lowenheim, F.A., "Electroplating," McGraw-Hill Book Company, New Yo 1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO ₃ Dielectrics for Future Stacked-Capacitor DRAM," International Business Machines Journal of Research Development 43(3):367-382, May 1999.			(including A)	amor, 1	me, Date, Perment	rages, Etc.)		
1979, pp. 12-13, and 416-423. O2 Kotecki, D.E., et al., "(Ba, Sr)TiO ₃ Dielectrics for Future Stacked-Capacitor DRAM," <i>International Business Machines Journal of Research Developmen</i> 43(3):367-382, May 1999.								
DRAM," International Business Machines Journal of Research Developmen 43(3):367-382, May 1999.								
Examiner Date Considered		O2	DRAM," Intern	ational I	Business Machines J		•	
	Exa	miner			Date Considered			

^{*}Examiner: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

-2-